[redacted]

[redacted]	[redacted]	[redacted]	[redacted]
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-1	

Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2	kV

ELECTRICAL CHARACTERISTICS(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j=125 R_L =3.3kΩ	- -	MIN.	0.2	V

I_L I_{G-N}

ORDERING INFORMATION

J ST 60 Z -800 BW

J: JieJie Microelectronics Co., Ltd.

ST: Triacs

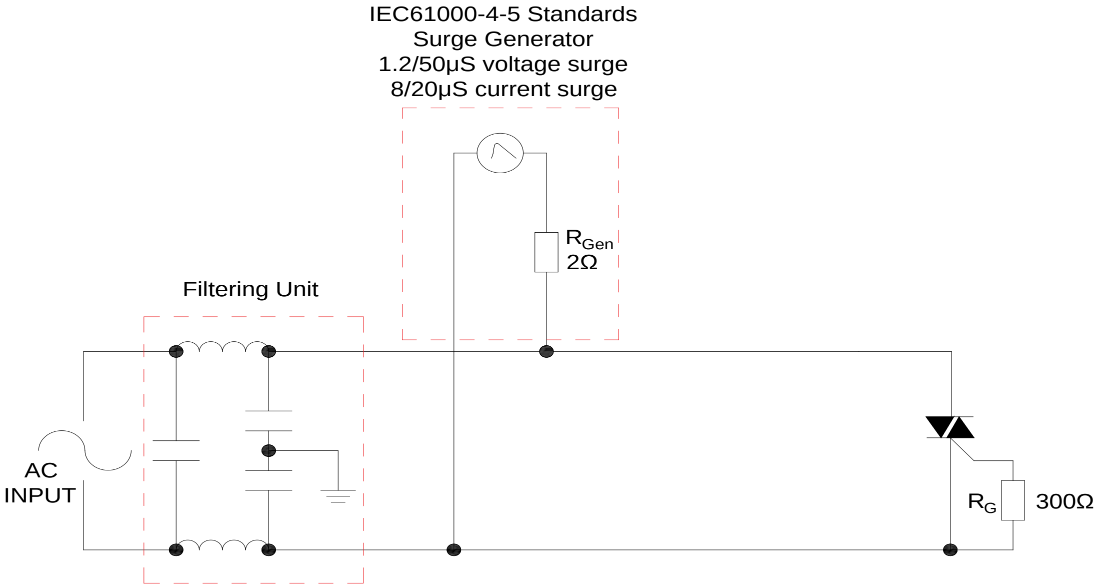
60: $I_{T(RMS)}$:60A

Z: Z:TO-3P(Ins)

-800: 800:V_{DRM} /$V_{RRM} \geq$ 800V

BW: BW:$I_{GT1-3} \leq$ 50mA

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM}(V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST60Z-800BW	800	50	TO-3P(Ins)	30	Tube

Document Revision History

Date	Revision	Changes
Apr.		

PACKAGE MECHANICAL DATA